

Silicon NPN Power Transistors

2N6465 2N6466

DESCRIPTION

- With TO-66 package
- Excellent safe operating area
- Complement to type 2N6467 2N6468

APPLICATIONS

- For use in audio amplifier applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector



Fig.1 simplified outline (TO-66) and symbol

Absolute maximum ratings($T_a = \square$)

SYMBOL	PARAMETER		CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	2N6465	Open emitter	110	V
		2N6466		130	
V_{CEO}	Collector-emitter voltage	2N6465	Open base	100	V
		2N6466		120	
V_{EBO}	Emitter-base voltage		Open collector	5	V
I_C	Collector current			4	A
P_D	Total power dissipation		$T_C = 25\square$	40	W
T_j	Junction temperature			150	$\square$
T_{stg}	Storage temperature			-65~150	$\square$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
$R_{th\ j-c}$	Thermal resistance junction to case	2.5	$\square/W$

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CHARACTERISTICS

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-emitter sustaining voltage	2N6465	$I_C=50mA ; I_B=0$	100			V
		2N6466		120			
V_{CEsat}	Collector-emitter saturation voltage		$I_C=1.5A ; I_B=0.15A$			1.2	V
V_{BE}	Base-emitter on voltage		$I_C=1.5A ; V_{CE}=4V$			1.5	V
I_{CBO}	Collector cut-off current	2N6465	$V_{CB}=110V ; I_E=0$			10	μA
		2N6466	$V_{CB}=130V ; I_E=0$				
I_{CEO}	Collector cut-off current	2N6465	$V_{CE}=100V, I_B=0$			100	μA
		2N6466	$V_{CE}=120V, I_B=0$				
I_{EBO}	Emitter cut-off current		$V_{EB}=5V ; I_C=0$			10	μA
h_{FE}	DC current gain		$I_C=1.5A ; V_{CE}=4V$	15		150	
f_T	Transition frequency		$I_C=0.5A ; V_{CE}=10V$	5			MHz

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PACKAGE OUTLINE

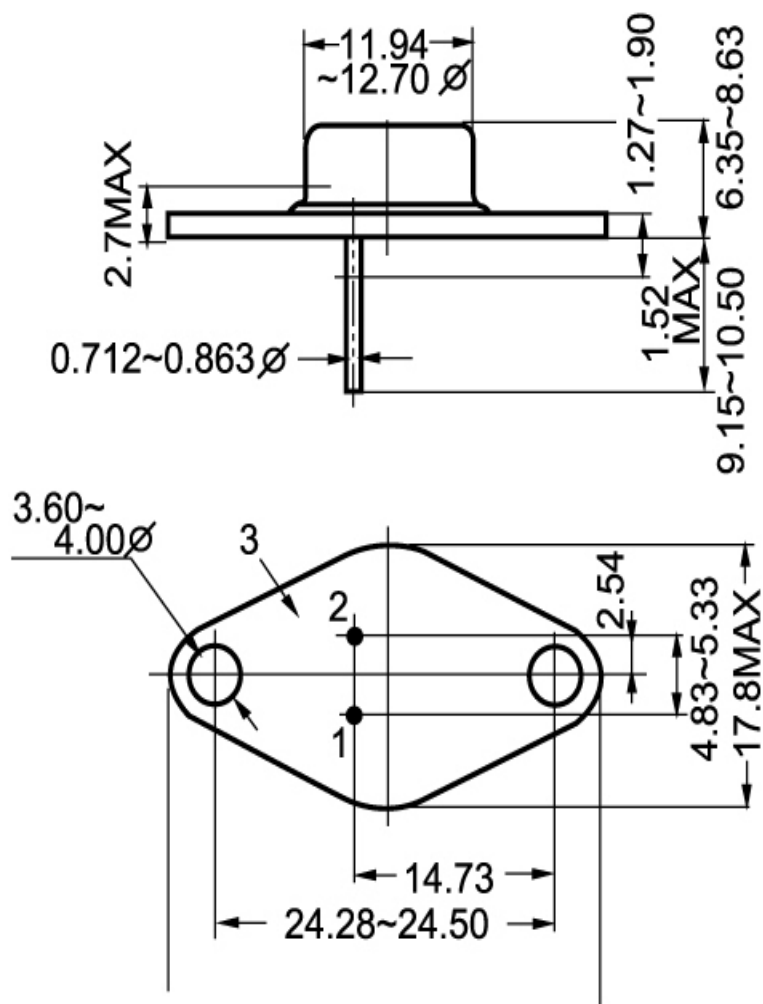


Fig.2 outline dimensions